NPN SILICON RF POWER TRANSISTOR BLW75

Description:
N-P-N silicon planar epitaxial transistor intended for transmitting applications in class-A, B or C in the UHF and VHF range for nominal supply voltages up to 25V. Designed for 25V Large-Signal Amplifier Applications, TV Transposers, and Transmitters Operating in Band 3, 220MHz.

Features:
SOT122 package. All leads are isolated from the flange.

Data:

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CER}	I_C = 50 mA	R_{BE} = 10 Ω		60			V
BV_{CBO}	I_C = 50 mA			60			V
BV_{CEO}	I_C = 50 mA			30			V
BV_{EBO}	I_E = 10 mA			4.0			V
h_{FE}	V_{CE} = 25 V	I_C = 2.0 A		20	45		---
C_{ob}	V_{CB} = 30 V		f = 1.0 MHz		90	120	pF
C_{re}	V_{CE} = 30 V	I_C = 200 mA	f = 1.0 MHz		55		pF
f_T	V_{CE} = 25 V	I_C = 6.0 A	f = 100 MHz		800		MHz

Drawings:

PIN CONFIGURATION

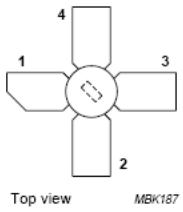
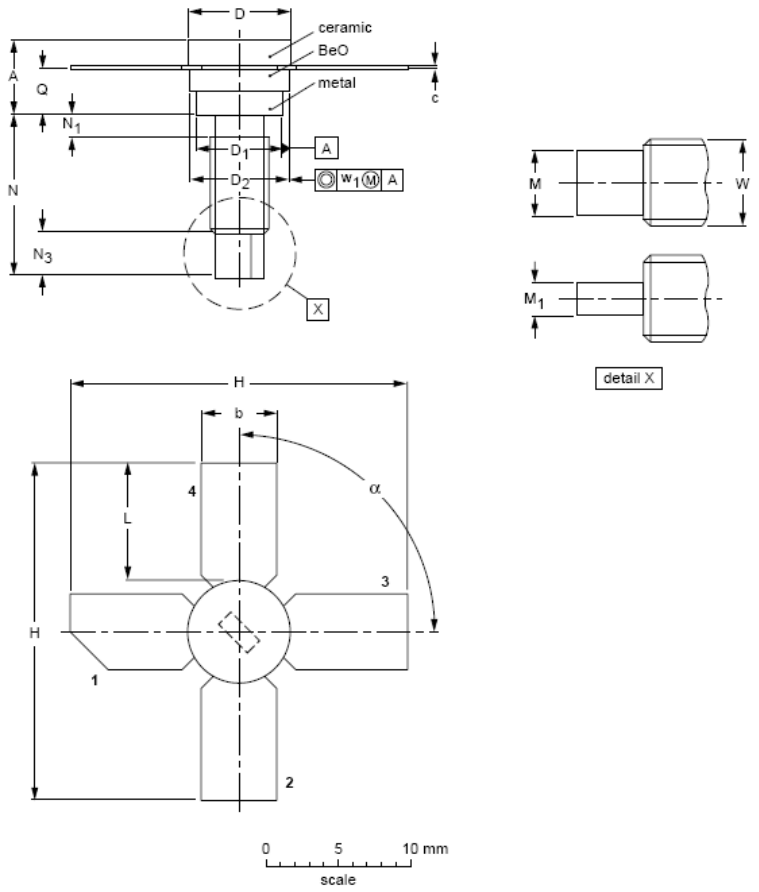


Fig.1 Simplified outline. SOT122A.

PINNING - SOT122A.

PIN	DESCRIPTION
1	collector
2	emitter
3	base
4	emitter

Studded ceramic package; 4 leads **SOT122A**



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D_1	D_2	H	L	M_1	M	N	N_1 max.	N_3	Q	W	w_1	α
mm	5.97 4.74	5.85 5.58	0.18 0.14	7.50 7.23	6.48 6.22	7.24 6.93	27.56 25.78	9.91 9.14	3.18 2.66	1.66 1.39	11.82 11.04	1.02	3.86 2.92	3.38 2.74	8-32 UNC	0.381	90°

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT122A						97-04-18